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(54) Title: A TECHNIQUE FOR ENHANCING TRANSISTOR PERFORMANCE BY TRANSISTOR SPECIFIC CONTACT DESIGN

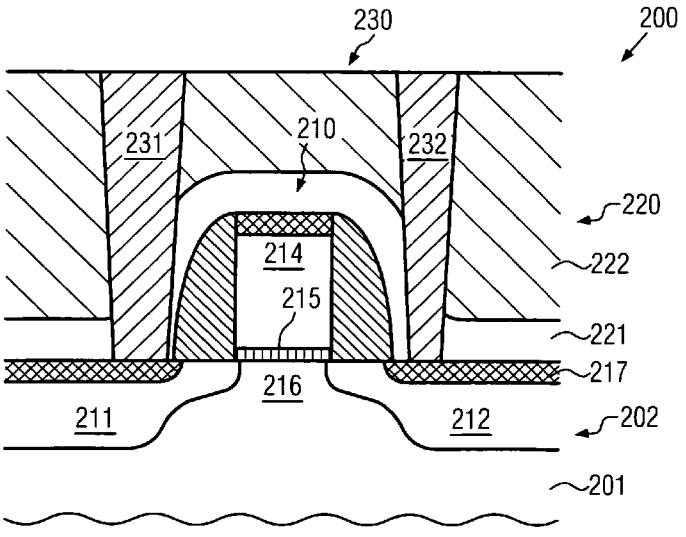


FIG. 2b

(57) Abstract: By locally adapting the size and/or density of a contact structure (230A, 230B), for instance, within individual transistors (210, 210A, 210B) or in a more global manner, the overall performance of advanced semiconductor devices (200) may be increased. Hence, the mutual interaction between the contact structure (230A, 230B) and local device characteristics may be taken into consideration. On the other hand, a high degree of compatibility with conventional process strategies may be maintained.

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